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Notice of Allowability	Application No.	Applicant(s)
	10/734,294	CHA, SEON YONG
	Examiner	Art Unit
	Thomas L. Dickey	2826
The MAILING DATE of this communication appears on the cover sheet with the correspondence address All claims being allowable, PROSECUTION ON THE MERITS IS (OR REMAINS) CLOSED in this application. If not included herewith (or previously mailed), a Notice of Allowance (PTOL-85) or other appropriate communication will be mailed in due course. THIS NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHTS. This application is subject to withdrawal from issue at the initiative of the Office or upon petition by the applicant. See 37 CFR 1.313 and MPEP 1308.  1. This communication is responsive to Amendment filed 12/6/05.		
2. The allowed claim(s) is/are <u>2-4</u> .		
3.		
6. DEPOSIT OF and/or INFORMATION about the deposit of BIOLOGICAL MATERIAL must be submitted. Note the attached Examiner's comment regarding REQUIREMENT FOR THE DEPOSIT OF BIOLOGICAL MATERIAL.		
Attachment(s)  1. Notice of References Cited (PTO-892)  2. Notice of Draftperson's Patent Drawing Review (PTO-948)  3. Information Disclosure Statements (PTO-1449 or PTO/SB/08 Paper No./Mail Date  4. Examiner's Comment Regarding Requirement for Deposit of Biological Material	6. ☐ Interview Summary ( Paper No./Mail Date 8), 7. ☐ Examiner's Amendm	ė

Application/Control Number: 10/734,294

Art Unit: 2826

## **REASONS FOR ALLOWANCE**

1. The following is an examiner's statement of reasons for allowance:

Claims 2-4 are allowed over the references of record because none of these references disclosed or can be combined to yield the claimed invention such as an MRAM including at least a vertical structure field effect transistor having a contact line, a magnetic tunnel junction (MTJ) cell, a bit line and a write word line sequentially formed on a drain area which is formed on a channel column, wherein the MTJ cell is formed by sequentially stacking a anti-ferroelectric thin film, a pinned ferromagnetic thin film, an insulation layer and a free ferromagnetic thin film on a contact line, as recited in claim 2.

Cha 2004/0175887 discloses an MRAM including each and every feature of claim 2, except that where claim 2 requires an anti-ferroelectric film, Cha discloses a semi-magnetic film.

2. Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

## Conclusion

3. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Thomas L Dickey whose telephone number is

Art Unit: 2826

571-272-1913. The examiner can normally be reached on Monday-Thursday 8-6.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nathan J Flynn can be reached on 571-272-1915. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Thomas L. Dickey Patent Examiner Art Unit 2826 12/05

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